Document Title

32Kx8 bit Low Power CMOS Static RAM

Revision History

Revision No	History	Draft Data	Remark
0.0	Initial draft	May 18, 1997	Design target
0.1	First revision - KM62256DL/DLI I_{SB1} = 100 → 50µA KM62256DL-L I_{SB1} = 20 → 10µA KM62256DLI-L I_{SB1} = 50 → 15µA - C_{IN} = 6 → 8pF, C_{IO} = 8 → 10pF - KM62256D-4/5/7 Family tOH = 5 → 10ns - KM62256DL/DLI I_{DR} = 50→30µA KM62256DL-L/DLI-L I_{DR} = 30 → 15µA	April 1, 1997	Preliminily
1.0	Finalize - Remove I_{CC} write value - Improved operating current I_{CC2} = 70 → 60mA - Improved standby current KM62256DL/DLI I_{SB1} = 50 → 30µA KM62256DL-L I_{SB1} = 10 → 5µA KM62256DLI-L I_{SB1} = 15 → 5µA - Improved data retention current KM62256DL/DLI I_{DR} = 30 → 5µA KM62256DL-L/DLI-L I_{DR} = 15 → 3µA - Remove 45ns part from commercial product and 100ns part from industrial product. Replace test load 100pF to 50pF for 55ns part	November 11, 1997	Final

32Kx8 bit Low Power CMOS Static RAM

FEATURES

- Process Technology : TFT
- Organization : 32Kx8
- Power Supply Voltage : 4.5~5.5V
- Low Data Retention Voltage : 2V(Min)
- Three state output and TTL Compatible
- Package Type : 28-DIP-600B, 28-SOP-450
  28-TSOP1-0813.4 F/R

GENERAL DESCRIPTION

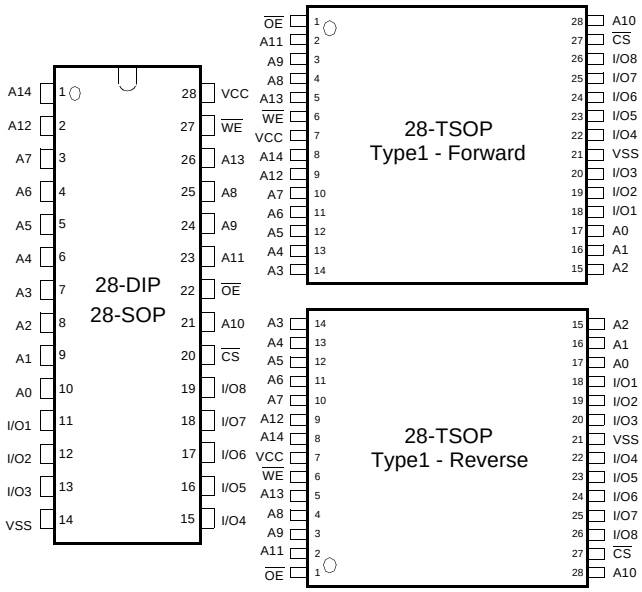
The K6T0808C1D families are fabricated by SAMSUNG′s advanced CMOS process technology. The families support various operating temperature ranges and have various package types for user flexibility of system design. The families also support low data retention voltage for battery back-up operation with low data retention current.

PRODUCT FAMILY

Product Family	Operating Temperature	Vcc Range	Speed	Power Dissipation		PKG Type
				Standby (I_{SB1}, Max)	Operating (I_{CC2}, Max)	
K6T0808C1D-L	Commercial (0~70°C)	4.5 to 5.5V	55[1]/70ns	30μA	60mA	28-DIP,28-SOP
K6T0808C1D-B				5μA		28-TSOP1-F/R
K6T0808C1D-P	Industrial (-40~85°C)		70ns	30μA		28-SOP
K6T0808C1D-F				5μA		28-TSOP1-F/R

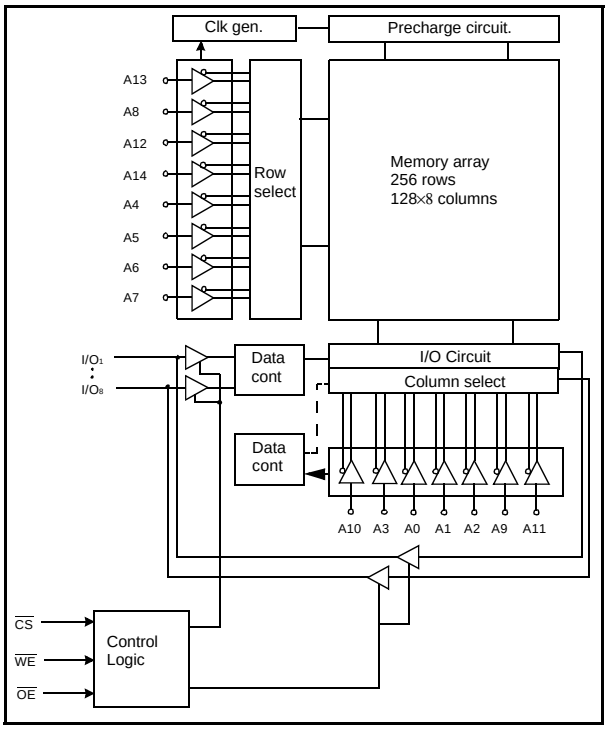
1. The parameter is tested with 50pF test load.

PIN DESCRIPTION



Pin Name	Function	Pin Name	Function
$\overline{CS}$	Chip Select Input	I/O_1~I/O_8	Data Inputs/Outputs
$\overline{OE}$	Output Enable Input	Vcc	Power
$\overline{WE}$	Write Enable Input	Vss	Ground
A_0~A_{14}	Address Inputs	NC	No connect

FUNCTIONAL BLOCK DIAGRAM



PRODUCT LIST

Commercial Temperature Products(0~70°C)		Industrial Temperature Products(-40~85°C)	
Part Name	**Function**	**Part Name**	**Function**
K6T0808C1D-DL55	28-DIP, 55ns, L-pwr	K6T0808C1D-GP70	28-SOP, 70ns, L-pwr
K6T0808C1D-DB55	28-DIP, 55ns, LL-pwr	K6T0808C1D-GF70	28-SOP, 70ns, LL-pwr
K6T0808C1D-DL70	28-DIP, 70ns, L-pwr	K6T0808C1D-TP70	28-TSOP1 F, 70ns, L-pwr
K6T0808C1D-DB70	28-DIP, 70ns, LL-pwr	K6T0808C1D-TF70	28-TSOP1 F, 70ns, LL-pwr
K6T0808C1D-GL55	28-SOP, 55ns, L-pwr	K6T0808C1D-RP70	28-TSOP1 R, 70ns, L-pwr
K6T0808C1D-GB55	28-SOP, 55ns, LL-pwr	K6T0808C1D-RF70	28-TSOP1 R, 70ns, LL-pwr
K6T0808C1D-GL70	28-SOP, 70ns, L-pwr		
K6T0808C1D-GB70	28-SOP, 70ns, LL-pwr		
K6T0808C1D-TL55	28-TSOP1 F, 55ns, L-pwr		
K6T0808C1D-TB55	28-TSOP1 F, 55ns, LL-pwr		
K6T0808C1D-TL70	28-TSOP1 F, 70ns, L-pwr		
K6T0808C1D-TB70	28-TSOP1 F, 70ns, LL-pwr		
K6T0808C1D-RL55	28-TSOP1 R, 55ns, L-pwr		
K6T0808C1D-RB55	28-TSOP1 R, 55ns, LL-pwr		
K6T0808C1D-RL70	28-TSOP1 R, 70ns, L-pwr		
K6T0808C1D-RB70	28-TSOP1 R, 70ns, LL-pwr		

FUNCTIONAL DESCRIPTION

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	I/O	Mode	Power
H	X[1)]	X[1)]	High-Z	Deselected	Standby
L	H	H	High-Z	Output Disabled	Active
L	L	H	Dout	Read	Active
L	X[1)]	L	Din	Write	Active

1. X means don't care (Must be in high or low states)

ABSOLUTE MAXIMUM RATINGS[1)]

Item	Symbol	Ratings	Unit	Remark
Voltage on any pin relative to Vss	V_{IN},V_{OUT}	-0.5 to 7.0	V	-
Voltage on Vcc supply relative to Vss	V_{CC}	-0.5 to 7.0	V	-
Power Dissipation	P_D	1.0	W	-
Storage temperature	T_{STG}	-65 to 150	°C	-
Operating Temperature	T_A	0 to 70	°C	K6T0808C1D-L
		-40 to 85	°C	K6T0808C1D-P
Soldering temperature and time	T_{SOLDER}	260°C, 10sec (Lead Only)	-	-

1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS[1)]

Item	Symbol	Min	Typ	Max	Unit
Supply voltage	Vcc	4.5	5.0	5.5	V
Ground	Vss	0	0	0	V
Input high voltage	V_{IH}	2.2	-	Vcc+0.5V[2)]	V
Input low voltage	V_{IL}	-0.5[3)]	-	0.8	V

Note:
1. Commercial Product : T_A=0 to 70°C, otherwise specified
   Industrial Product : T_A=-40 to 85°C, otherwise specified
2. Overshoot : V_{CC}+3.0V in case of pulse width≤30ns
3. Undershoot : -3.0V in case of pulse width≤30ns
4. Overshoot and undershoot are sampled, not 100% tested

CAPACITANCE[1)] (f=1MHz, T_A=25°C)

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	C_{IN}	V_{IN}=0V	-	8	pF
Input/Output capacitance	C_{IO}	V_{IO}=0V	-	10	pF

1. Capacitance is sampled not, 100% tested

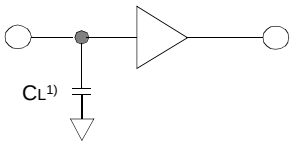
DC AND OPERATING CHARACTERISTICS

Item	Symbol	Test Conditions		Min	Typ	Max	Unit
Input leakage current	I_{LI}	V_{IN}=Vss to Vcc		-1	-	1	µA
Output leakage current	I_{LO}	$\overline{CS}$=V_{IH} or $\overline{OE}$=V_{IH} or $\overline{WE}$=V_{IL}, V_{IO}=Vss to Vcc		-1	-	1	µA
Operating power supply current	I_{CC}	I_{IO}=0mA, $\overline{CS}$=V_{IL}, V_{IN}=V_{IH} or V_{IL}, Read		-	5	10	mA
Average operating current	I_{CC1}	Cycle time=1µs, 100% duty, I_{IO}=0mA $\overline{CS}$≤0.2V, V_{IN}≤0.2V, V_{IN}≥Vcc -0.2V	Read	-	2	5	mA
			Write		-	20	
	I_{CC2}	Cycle time=Min,100% duty, I_{IO}=0mA, $\overline{CS}$=V_{IL}, V_{IN}=V_{IH} or V_{IL}		-	45	60	mA
Output low voltage	V_{OL}	I_{OL}=2.1mA		-	-	0.4	V
Output high voltage	V_{OH}	I_{OH}=-1.0mA		2.4	-	-	V
Standby Current(TTL)	I_{SB}	$\overline{CS}$=V_{IH}, Other inputs=V_{IH} or V_{IL}		-	-	1	mA
Standby Current (CMOS)	I_{SB1}	$\overline{CS}$≥Vcc-0.2V, Other inputs=0~Vcc	Low Power	-	1	30	µA
			Low Low Power	-	0.2	5	µA

AC OPERATING CONDITIONS

TEST CONDITIONS (Test Load and Test Input/Output Reference)

Input pulse level : 0.8 to 2.4V
Input rising and falling time : 5ns
Input and output reference voltage : 1.5V
Output load (See right) :C_L=100pF+1TTL
C_L=50pF+1TTL



1. Including scope and jig capacitance

AC CHARACTERISTICS (V_{CC}=4.5~5.5V, K6T0808C1D-L Family:T_A=0 to 70°C, K6T0808C1D-P Family:T_A=-40 to 85°C)

Parameter List		Symbol	Speed Bins				Units
			55[1]ns		70ns		
			Min	Max	Min	Max	
Read	Read cycle time	t_{RC}	55	-	70	-	ns
	Address access time	t_{AA}	-	55	-	70	ns
	Chip select to output	t_{CO}	-	55	-	70	ns
	Output enable to valid output	t_{OE}	-	25	-	35	ns
	Chip select to low-Z output	t_{LZ}	10	-	10	-	ns
	Output enable to low-Z output	t_{OLZ}	5	-	5	-	ns
	Chip disable to high-Z output	t_{HZ}	0	20	0	30	ns
	Output disable to high-Z output	t_{OHZ}	0	20	0	30	ns
	Output hold from address change	t_{OH}	10	-	10	-	ns
Write	Write cycle time	t_{WC}	55	-	70	-	ns
	Chip select to end of write	t_{CW}	45	-	60	-	ns
	Address set-up time	t_{AS}	0	-	0	-	ns
	Address valid to end of write	t_{AW}	45	-	60	-	ns
	Write pulse width	t_{WP}	40	-	50	-	ns
	Write recovery time	t_{WR}	0	-	0	-	ns
	Write to output high-Z	t_{WHZ}	0	20	0	25	ns
	Data to write time overlap	t_{DW}	25	-	30	-	ns
	Data hold from write time	t_{DH}	0	-	0	-	ns
	End write to output low-Z	t_{OW}	5	-	5	-	ns

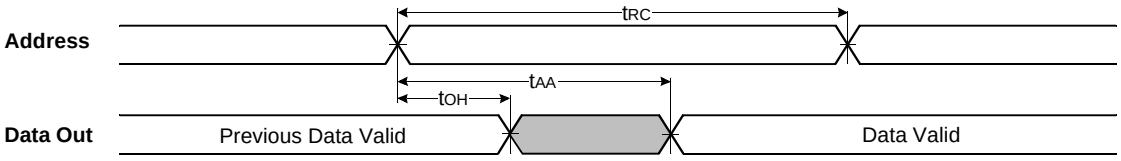
1. The parameter is tested with 50pF test load.

DATA RETENTION CHARACTERISTICS

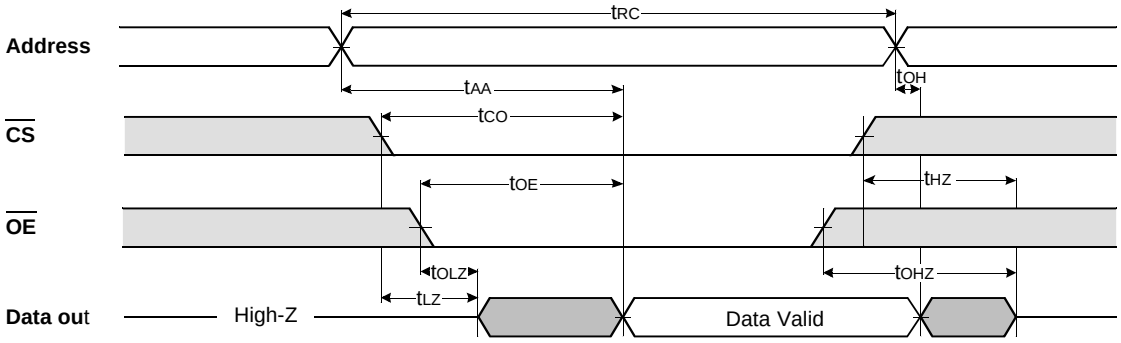
Item	Symbol	Test Condition		Min	Typ	Max	Unit
Vcc for data retention	V_{DR}	$\overline{CS}$≥Vcc-0.2V		2.0	-	5.5	V
Data retention current	I_{DR}	Vcc=3.0V, $\overline{CS}$≥Vcc-0.2V	L-Ver	-	1	15	µA
			LL-Ver	-	0.2	3	
Data retention set-up time	t_{SDR}	See data retention waveform		0	-	-	ms
Recovery time	t_{RDR}			5	-	-	

TIMMING DIAGRAMS

TIMING WAVEFORM OF READ CYCLE(1) (Address Controlled, $\overline{CS}$=$\overline{OE}$=V_{IL}, $\overline{WE}$=V_{IH})



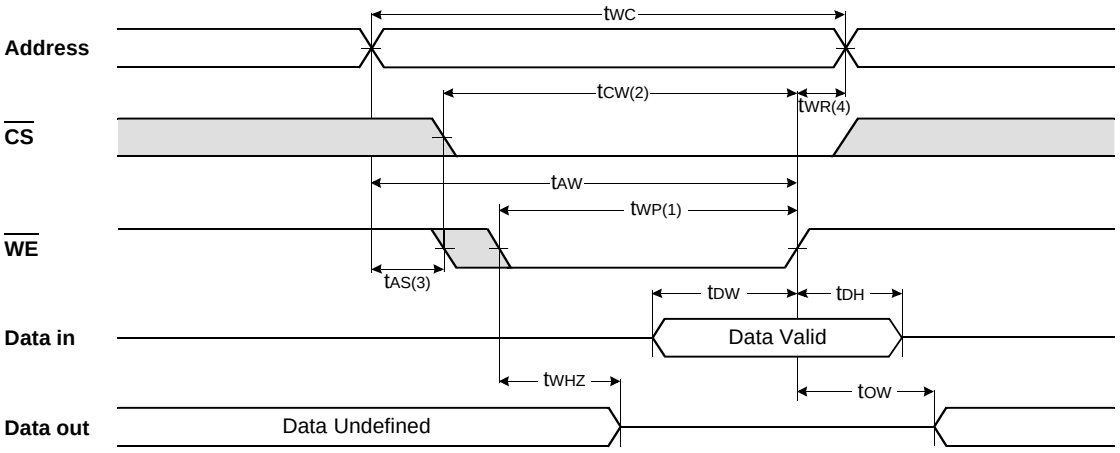
TIMING WAVEFORM OF READ CYCLE(2) ($\overline{WE}$=V_{IH})



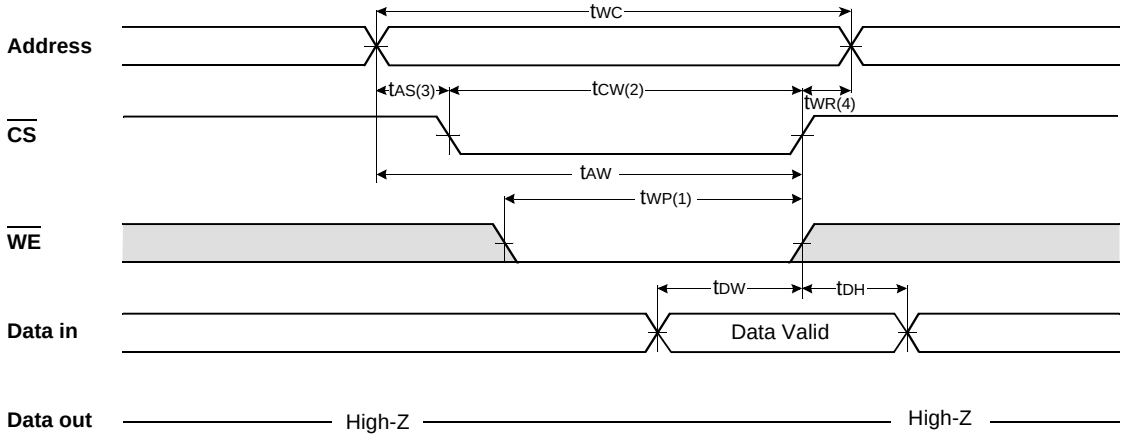
NOTES (READ CYCLE)

1. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition, t_{HZ}(Max.) is less than t_{LZ}(Min.) both for a given device and from device to device interconnection.

TIMING WAVEFORM OF WRITE CYCLE(1) (WE Controlled)



TIMING WAVEFORM OF WRITE CYCLE(2) ($\overline{CS}$ Controlled)

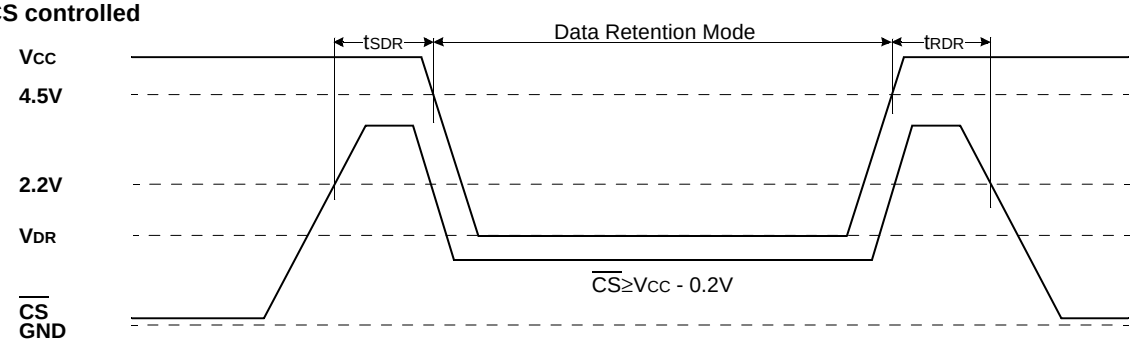


NOTES (WRITE CYCLE)

1. A write occurs during the overlap of a low $\overline{CS}$ and a low $\overline{WE}$. A write begins at the latest transition among $\overline{CS}$ going Low and $\overline{WE}$ going low : A write end at the earliest transition among $\overline{CS}$ going high and $\overline{WE}$ going high, t_{WP} is measured from the begining of write to the end of write.
2. t_{CW} is measured from the $\overline{CS}$ going low to end of write.
3. t_{AS} is measured from the address valid to the beginning of write.
4. t_{WR} is measured from the end of write to the address change. t_{WR} applied in case a write ends as $\overline{CS}$ or $\overline{WE}$ going high.

DATA RETENTION WAVE FORM

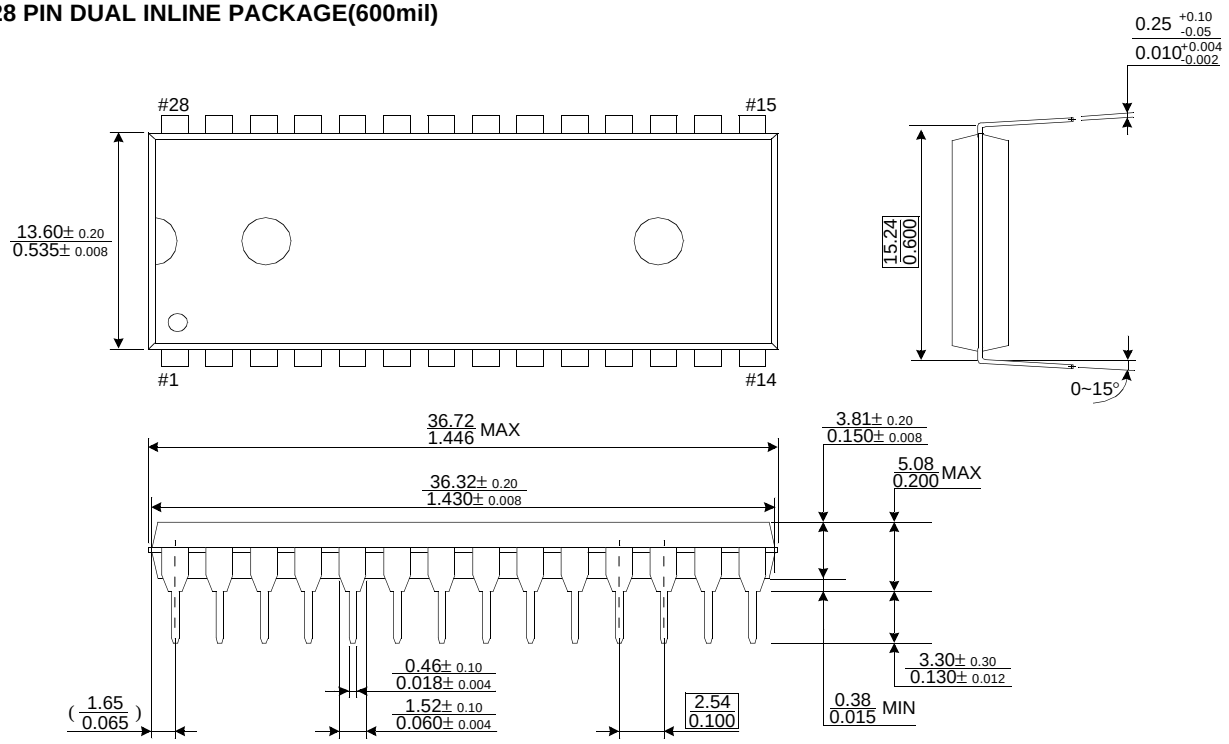
$\overline{CS}$ controlled



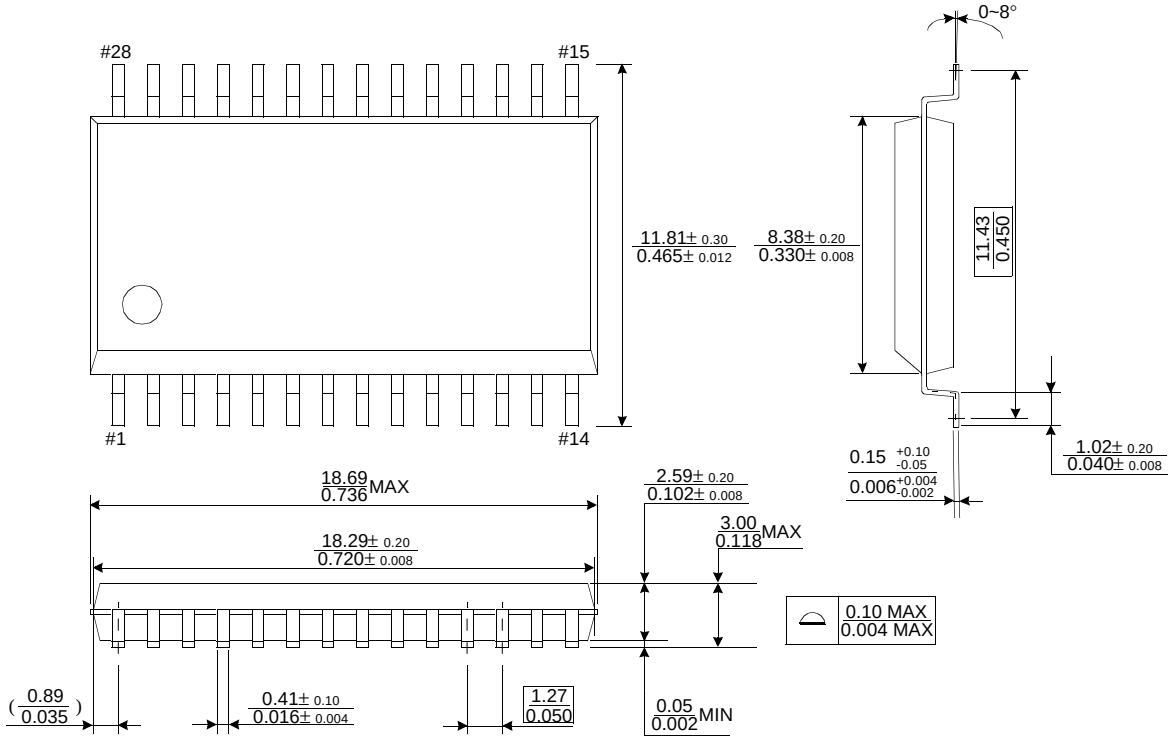
PACKAGE DIMENSIONS

Units: millimeter(inch)

28 PIN DUAL INLINE PACKAGE(600mil)



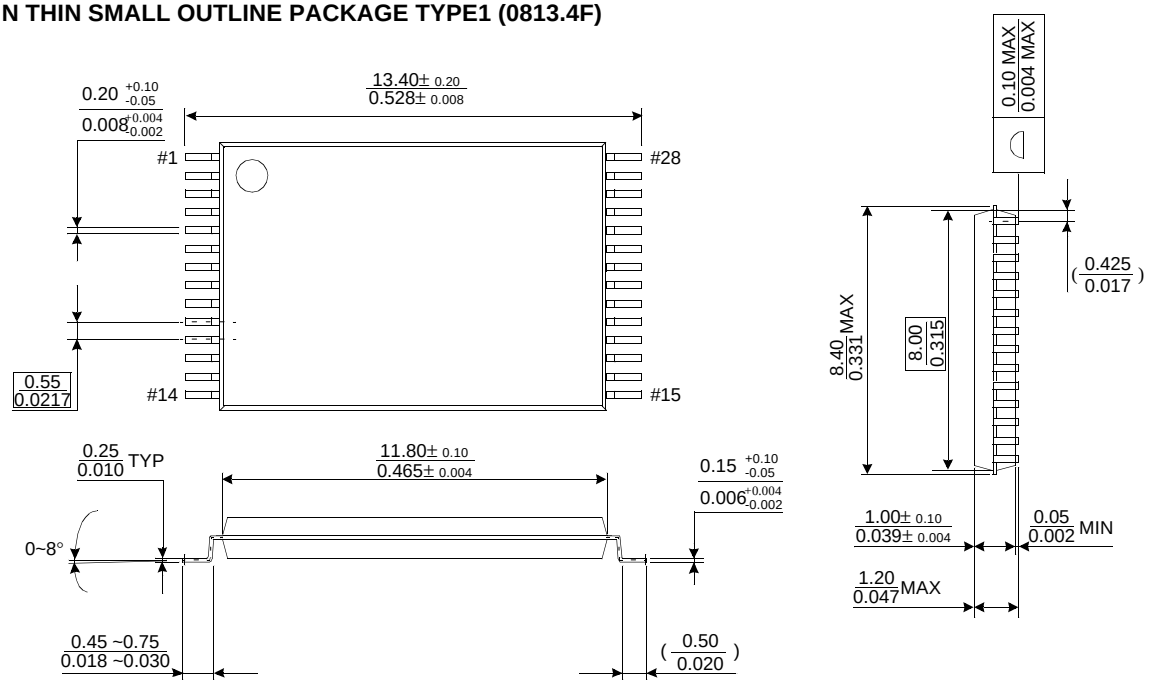
28 PIN PLASTIC SMALL OUTLINE PACKAGE(450mil)



PACKAGE DIMENSIONS

Units: millimeter(inch)

28 PIN THIN SMALL OUTLINE PACKAGE TYPE1 (0813.4F)



28 PIN THIN SMALL OUTLINE PACKAGE TYPE1 (0813.4R)